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Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 50 A



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PRODUCT SUMMARY						
Package	TO-247L					
I _{T(AV)}	50 A					
V _{DRM} /V _{RRM}	1200 V					
V _{TM} (typ.)	1.1 V					
I _{GT} (typ.)	40 mA					
T _J max.	150 °C					
Diode variation	Single SCR					

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- 150 °C maximum operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>
 HALOGEN

APPLICATIONS

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-50TPS12 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 $^{\circ}$ C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	V _{RRM} /V _{DRM}		1200	V				
On-state voltage	V _T	50 A, T _J = 125 °C	1.1	v				
Average rectified forward current	I _{T(AV)}		50					
Maximum continuous RMS on-state current	I _{RMS}		79	А				
Non-repetitive peak surge current	I _{TSM}		630					
Maximum rate of rise	dV/dt		1000	V/µs				
Operating junction and storage temperature range	T _J , T _{Stg}		-40 to +150	°C				

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA
VS-50TPS12L-M3	1200	1300	10

VS-50TPS12L-M3



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ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	$T_C = 112$ °C, 180° conduction half sine v	vave	-	50	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}			-	79	А
Peak, one-cycle non-repetitive surge current	L	10 ms sine pulse, rated V_{RRM} applied		-	530	
reak, one-cycle non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied	Initial $T_J = T_J$	-	630	
12t for funing	l ² t	10 ms sine pulse, rated V_{RRM} applied	maximum	-	1405	A ² s
I ² t for fusing	1-1	10 ms sine pulse, no voltage reapplied		-	1986	
I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, T_J = 125 °C		-	19 850	A²√s
Low level value of threshold voltage	V _{T(TO)1}				0.89	v
High level value of threshold voltage	V _{T(TO)2}	T.ı = 125 °C	-	0.97	v	
Low level value of on-state slope resistance	r _{t1}	1J= 125 C	-	6.77	mΩ	
High level value of on-state slope resistance	r _{t2}			-	6.32	ms2
	V	50 A, T _J = 25 °C			1.32	v
On-state voltage	V _T	100 A, T _J = 25 °C			1.6	v
Rate of rise of turned-on current	dl/dt	T _J = 25 °C		-	150	A/µs
Holding current	Ι _Η				300	
Latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$		-	350	
	1 /1	T _J = 25 °C			0.05	mA
Reverse and direct leakage current	I _{RRM} /I _{DRM}	T _J = 125 °C			10	
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V _{DRM} ,	$R_g - k = \infty \Omega$	-	1000	V/µs

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS
Peak gate power	P _{GM}		no voltago roopplied	-	10	w
Average gate power	P _{G(AV)}	to this sine puis	se, no voltage reapplied	-	2.5	vv
Peak gate current	I _{GM}			-	2.5	А
Peak negative gate voltage	-V _{GM}			-	10	
	V _{GT}	T _J = -40 °C	Anode supply = 6 V resistive load	-	1.6	v
Required DC gate voltage to trigger		T _J = 25 °C		-	1.5	v
		T _J = 150 °C		-	1	
		T _J = -40 °C		-	160	
Required DC gate to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	45	100	mA
		T _J = 150 °C		-	60	
DC gate voltage not to trigger	V _{GD}	T - 150 °C V	- rated value	-	0.2	V
DC gate current not to trigger	I _{GD}	$T_J = 150 \text{ °C}, V_{DRM} = \text{rated value}$				mA

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t _{gt}	I_T = 50 A, V_D = 50 % V_{DRM},I_{gt} = 300 mA, T_J = 25 °C	1.5	-	
Turn-off time	t _q	$\begin{array}{l} I_{T}=50 \text{ A}, V_{D}=80 \% V_{DRM}, dV/dt=20 V/\mu s, t_{p}=200 \mu s \\ I_{gt}=100 \text{mA}, dI/dt=10 A/\mu s, V_{R}=100 \text{V}, T_{J}=150 ^\circ \text{C} \end{array}$	92	-	μs

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THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS		
Maximum junction and storage tem	perature range	T _J , T _{Stg}		-40	150	°C		
Maximum thermal resistance, juncti	on to case	R _{thJC}		-	0.35			
Maximum thermal resistance, junction to ambient		R _{thJA}		-	40	°C/W		
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.2	-			
Mounting torque	minimum			6 (5)		kgf · cm (lbf · in)		
Mounting torque	maximum			12 (10)				
Marking device			Case style Super TO-247L	50TPS12L		Ĺ		

DEVICE	SINE HALF-WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION					
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-50TPS12L-M3	0.143	0.166	0.208	0.299	0.490	0.099	0.168	0.223	0.311	0.494	°C/W

Max. Average On-state Power Loss (W)

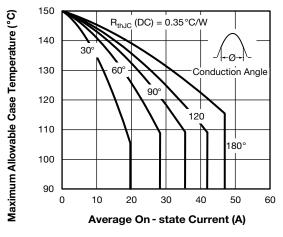
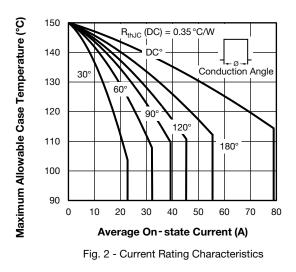


Fig. 1 - Current Rating Characteristics



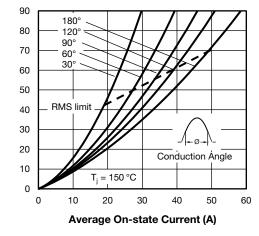
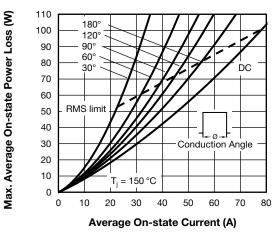
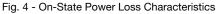


Fig. 3 - On-State Power Loss Characteristics



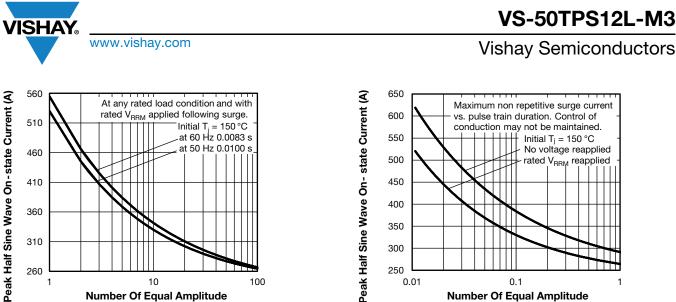


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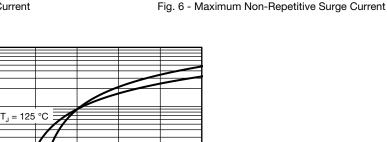


Half Cycle Current Pulse (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

1000

100



Half Cycle Current Pulse (N)

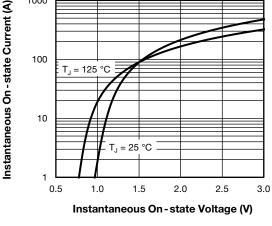
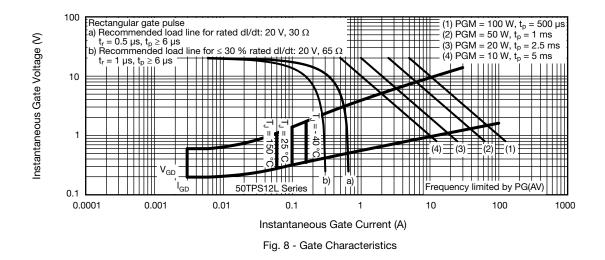


Fig. 7 - On-State Voltage Drop Characteristics



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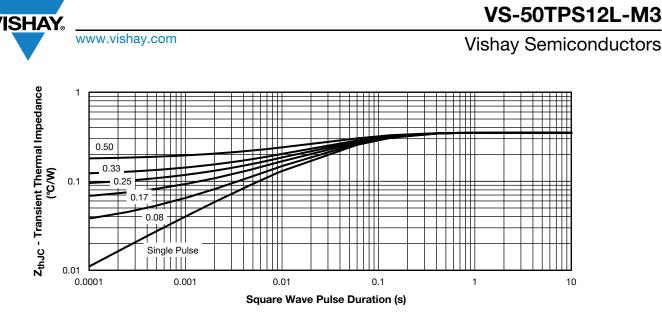


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	50	т	Р	s	12	L	-M3
		2	3	4	5	6	7	8
	2 3 4 5	- Cur - Circ - P = - Typ - Typ - Vol - Pac	rrent coor cuit conf thyristo TO-247 te of silit standar tage coor ckage L	' packag	50 A) n: ge ery rect 1200 V ead	ifier ′)		

ORDERING INFORMATION (example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-50TPS12L-M3	25	contact factory	Antistatic plastic tubes					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95626				
Part marking information	www.vishay.com/doc?95007				

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